P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
–30	0.0085 @ V_{GS} = –10 V	–14
	0.014 @ V_{GS} = –4.5 V	–11

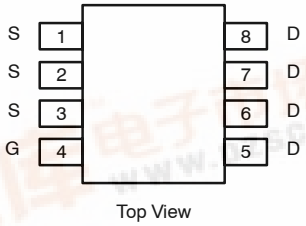
FEATURES

- TrenchFET® Power MOSFET
- ESD Protection: 3000 V

APPLICATIONS

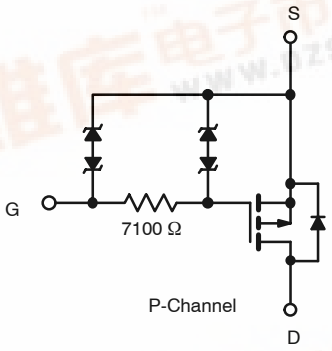
- Notebook PC
  - Load Switch
  - Adapter Switch

SO-8



Top View

Ordering Information: Si4483EDY-T1—E3



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	–30		V
Gate-Source Voltage		V_{GS}	±25		
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	–14	–10	A
	T_A = 70°C		–11	–8	
Pulsed Drain Current		I_{DM}	–50		
Continuous Source Current (Diode Conduction)[a]		I_S	–2.7	–1.36	
Maximum Power Dissipation[a]	T_A = 25°C	P_D	3.0	1.5	W
	T_A = 70°C		1.9	0.95	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	33	42	°C/W
	Steady State		70	85	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	16	21	

Notes:
a. Surface Mounted on 1" x 1" FR4 Board.

SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

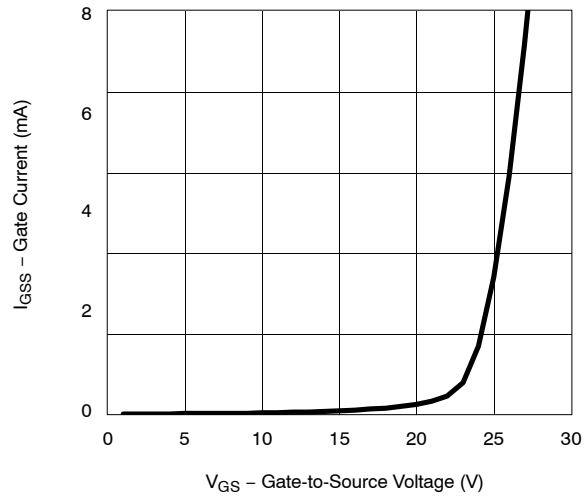
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = −250 μA	−1.0		3.0	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±4.5 V			±1	μA
		V_{DS} = 0 V, V_{GS} = ±25 V			±10	mA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = −30 V, V_{GS} = 0 V			−1	μA
		V_{DS} = −30 V, V_{GS} = 0 V, T_J = 70°C			−10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = −5 V, V_{GS} = −10 V	−30			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = −10 V, I_D = −14 A		0.007	0.0085	Ω
		V_{GS} = −4.5 V, I_D = −11 A		0.0115	0.014	
Forward Transconductance[a]	g_{fs}	V_{DS} = −15 V, I_D = −14 A		60		S
Diode Forward Voltage[a]	V_{SD}	I_S = −2.7 A, V_{GS} = 0 V		−0.74	−1.1	V
Dynamic[b]						
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = −15 V, R_L = 15 Ω I_D ≅ −1 A, V_{GEN} = −10 V, R_g = 6 Ω		10	15	μs
Rise Time	t_r			20	30	
Turn-Off Delay Time	$t_{d(off)}$			42	65	
Fall Time	t_f			50	80	

Notes
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

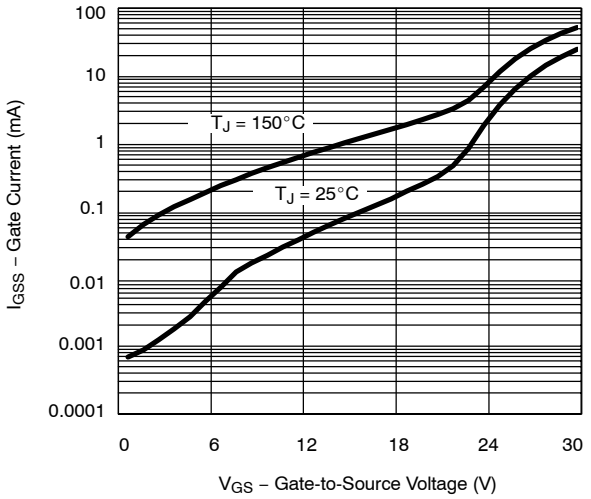
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

Gate-Current vs. Gate-Source Voltage

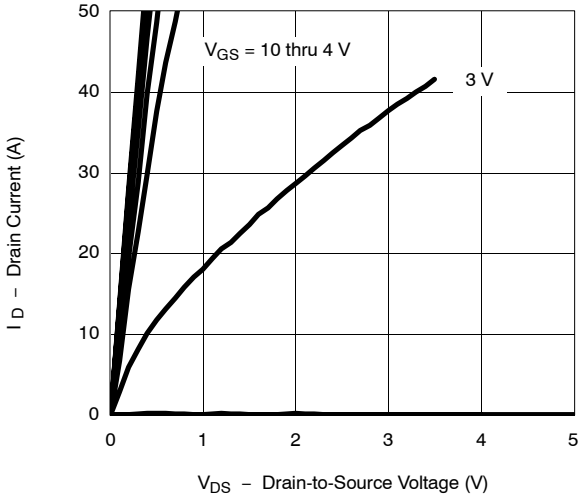


Gate Current vs. Gate-Source Voltage

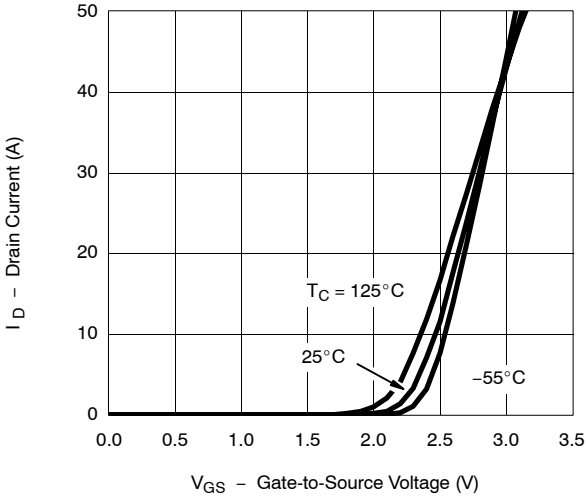


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

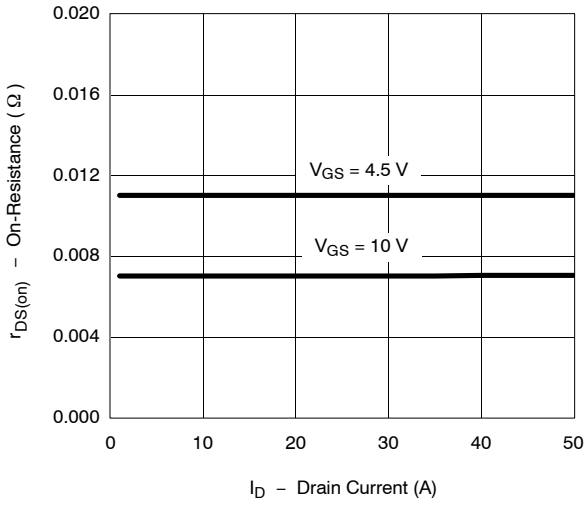
Output Characteristics



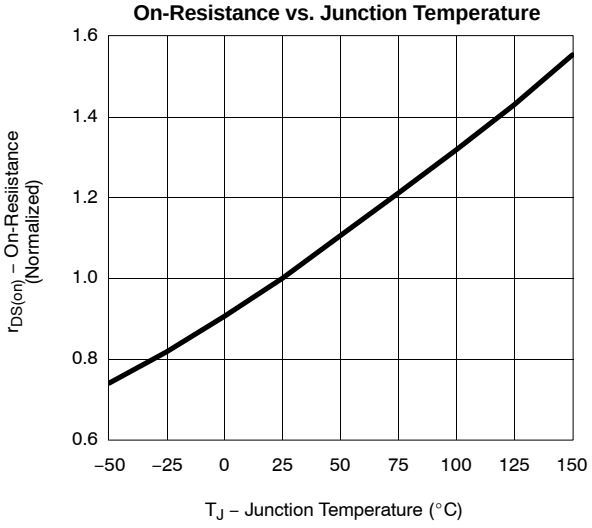
Transfer Characteristics



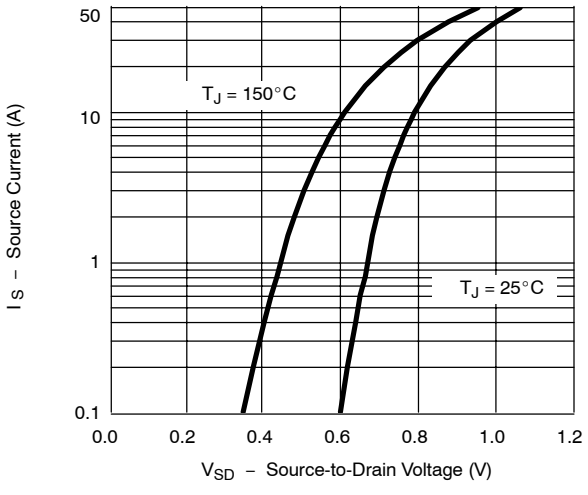
On-Resistance vs. Drain Current



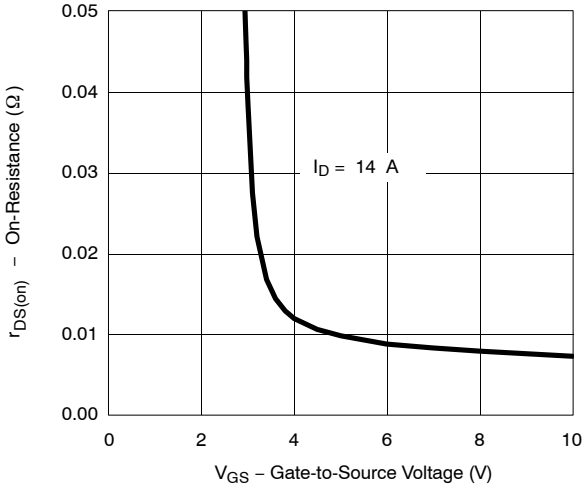
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

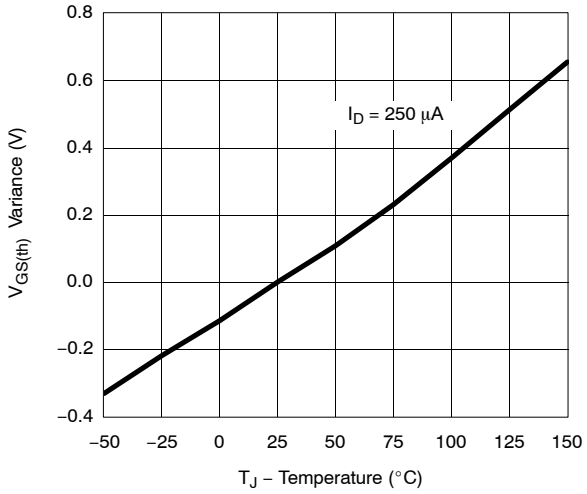


On-Resistance vs. Gate-to-Source Voltage

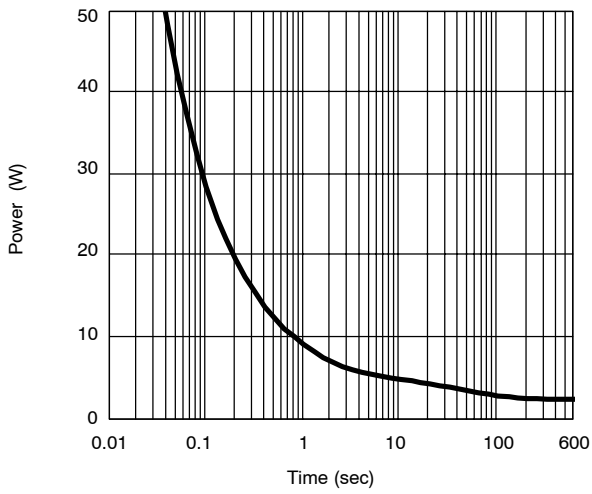


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

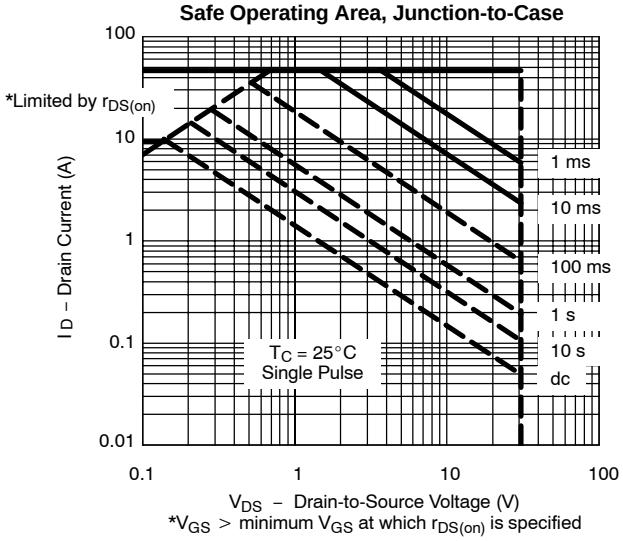
Threshold Voltage



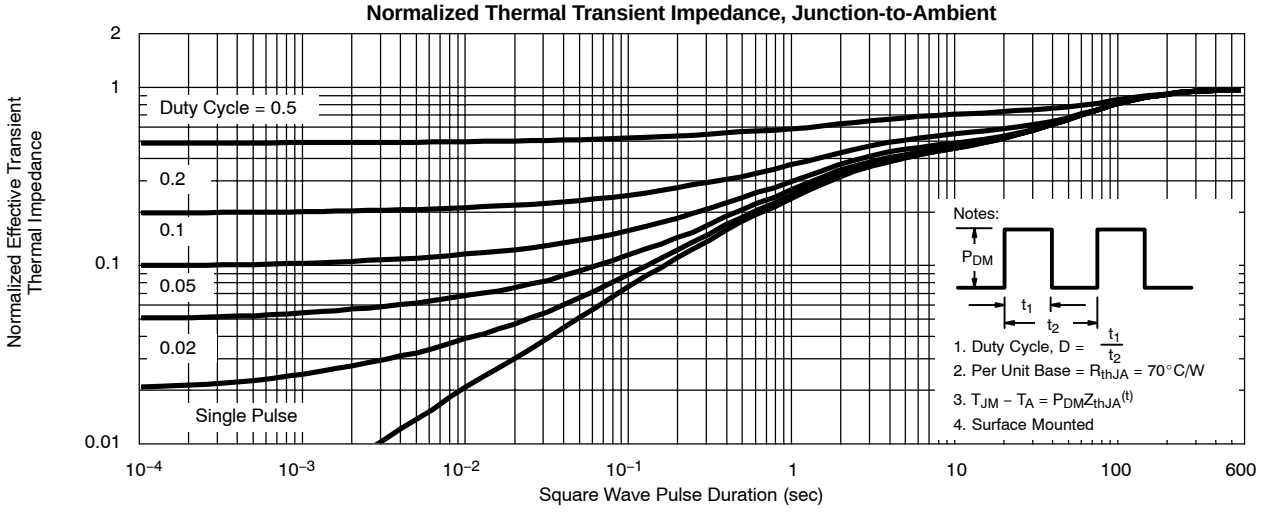
Single Pulse Power



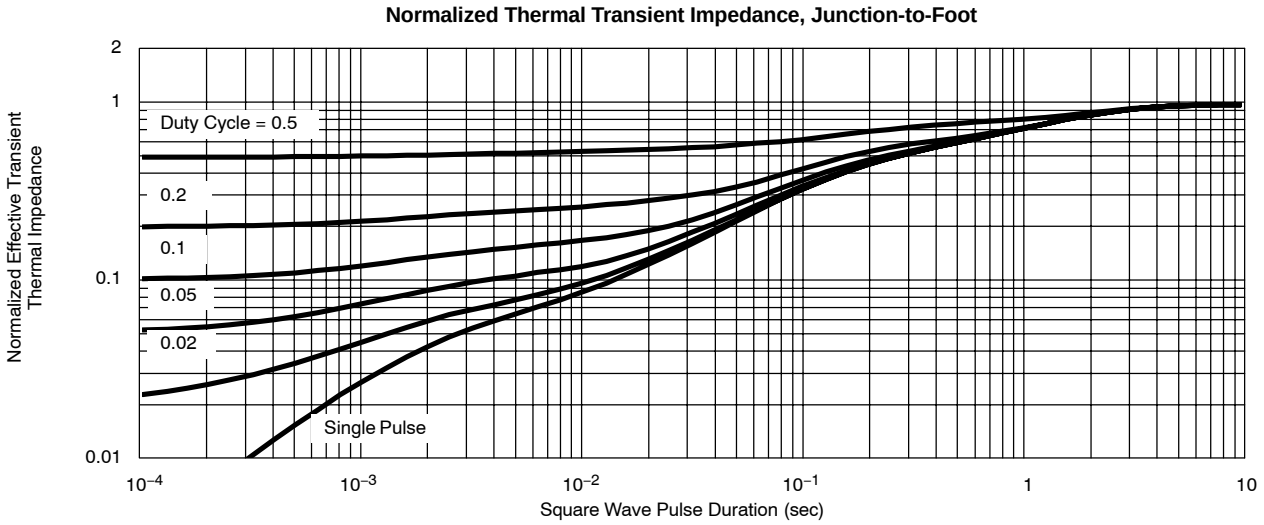
Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



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